BAW27

SILICON EPITAXIAL PLANAR DIODE

Features

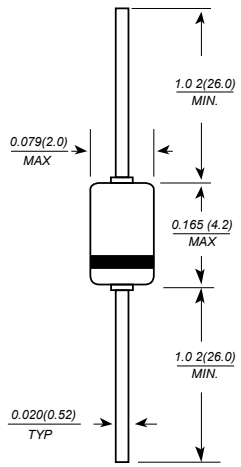
- Low forward voltage drop
- High forward current capability

Mechanical Data

- Case: DO-35 Glass Case
- Weight: approx. 0.13g

RoHS COMPLIANT

DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	75	V
Reverse voltage			V_R	60	V
Peak forward surge current	t_p=1μs		I_{FSM}	4	A
Forward current			I_F	600	mA
Average forward current	V_R=0		I_{FAV}	300	mA
Power dissipation	l=4mm, T_L=45°C		P_V	440	mW
	l=4mm, T_L≦25°C		P_V	500	mW
Junction temperature			T_j	200	°C
Storage temperature range			T_{stg}	–65...+200	°C

Maximum Thermal Resistance T_j = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	l=4mm, T_L=constant	R_{thJA}	350	K/W

Electrical Characteristics T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=10mA		V_F		0.67	0.75	V
	I_F=50mA		V_F		0.8	0.85	V
	I_F=200mA		V_F		0.95	1.0	V
	I_F=400mA		V_F		1.12	1.25	V
Reverse current	V_R=60V		I_R			100	nA
	V_R=60V, T_j=100°C		I_R			50	μA
Breakdown voltage	I_R=5μA, t_p/T=0.01, t_p=0.3ms		$V_{(BR)}$	75			V
Diode capacitance	V_R=0, f=1MHz, V_{HF}=50mV		C_D			4	pF
Reverse recovery time	I_F=I_R=10...100mA, i_R=0.1xI_R		t_{rr}			6	ns